RT3AMMAM1

Composite Transistor For Low Frequency Amplify Application Silicon Pnp Epitaxial Type

DESCRIPTION

RT3AMMAM1 is compound transistor built with two $ISA1235A\,chips$ in SC-88 package.

FEATURE

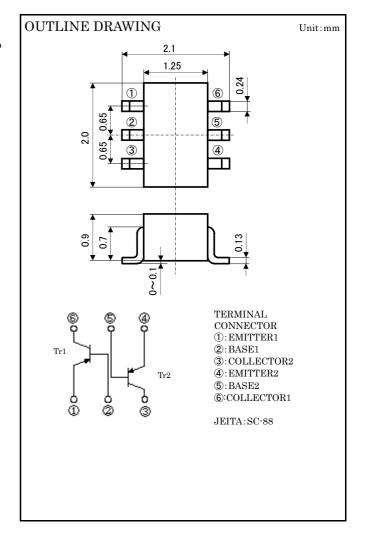
Silicon PNP epitaxial type

Each transistor elements are independent.

Mini package for easy mounting.

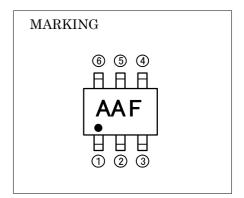
APPLICATION

For low frequency amplify application.



MAXIMUM RATING (Ta=25°C) (Tr1, Tr2.)

| SYMBOL | PARAMETER | RATING | UNIT |
|--------------------|--------------------------------------|----------|------|
| Vcbo | Collector to Base voltage | -60 | V |
| Vebo | Emitter to Base voltage | -6 | V |
| VCEO | Collector to Emitter voltage | -50 | V |
| Ic | Collector current | -200 | mA |
| PC | Collector dissipation(Total,Ta=25°C) | 150 | mW |
| Tj | Junction temperature | +150 | °C |
| T_{stg} | Storage temperature | -55~+150 | °C |



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ELECTRICAL CHARACTERISTICS (Ta=25°C) (Tr1, Tr2.)

| Symbol | Parameter | m | Limits | | | TT |
|----------|---|---|--------|-----|------|------|
| | | Test conditions | Min | Тур | Max | Unit |
| V(BR)CEO | Collector to Emitter break down voltage | I _C =100 μ A,R _{BE} =∞ | -50 | - | - | V |
| ICBO | Collector cut off current | V _{CB} =-60V,I _E =0 | - | - | -0.1 | μΑ |
| IEBO | Emitter cut off current | V _{EB} =-6V,I _C =0 | - | - | -0.1 | μΑ |
| hfe* | DC forward current gain | V _{CE} =-6V,I _C =-1mA | 150 | - | 500 | - |
| h_{FE} | DC forward current gain | V _{CE} =-6V,I _C =-0.1mA | 90 | - | - | - |
| VCE(sat) | Collector to Emitter saturation voltage | Ic=-100mA,I _B =-10mA | - | - | -0.3 | V |
| fT | Gain band width product | V _{CE} =-6V,I _E =10mA | - | 200 | - | MHz |
| Cob | Collector output capacitance | V _{CB} =-6V,I _E =0,f=1MH _Z | - | 4.0 | - | pF |
| NF | Noise figure | V_{CE} =6 V_{IE} =0.3 mA_{f} =100 H_{Z} , R_{G} =10 $k\Omega$ | - | - | 20 | dB |

 $oldsymbol{*}$: It shows hfe classification in right table.

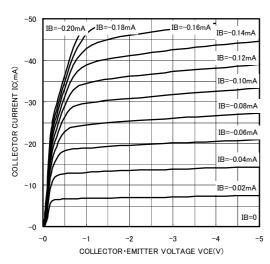
| item | E | F |
|------|---------|---------|
| hee | 150~300 | 250~500 |

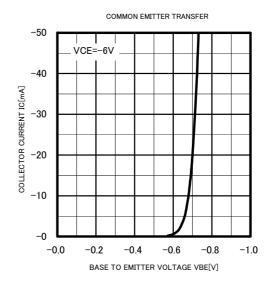
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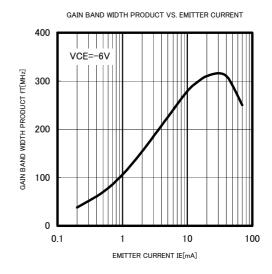
TYPICAL CHARACTERISTICS (Tr1,r2.)

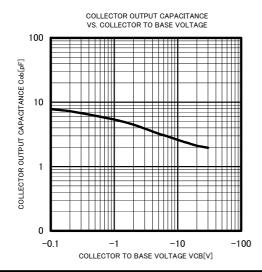
COMMON EMITTER OUTPUT





DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT VCE=-6V 1000@IC=-1mA) 10 -0.1 -1 -10 -100 -1000 COLLECTOR CURRENT IC[mA]







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